

CMLT591E
SURFACE MOUNT
PICOMini™
PNP SILICON TRANSISTOR



SOT-563 CASE

MAXIMUM RATINGS: ($T_A=25^\circ\text{C}$)

Collector-Base Voltage
Collector-Emitter Voltage
Emitter-Base Voltage
Collector Current
Base Current
Collector Current (Peak)
Power Dissipation
Operating and Storage
Junction Temperature
Thermal Resistance

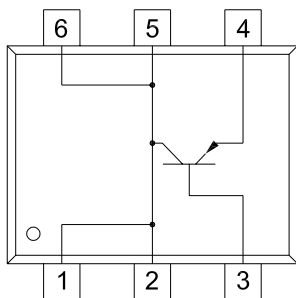
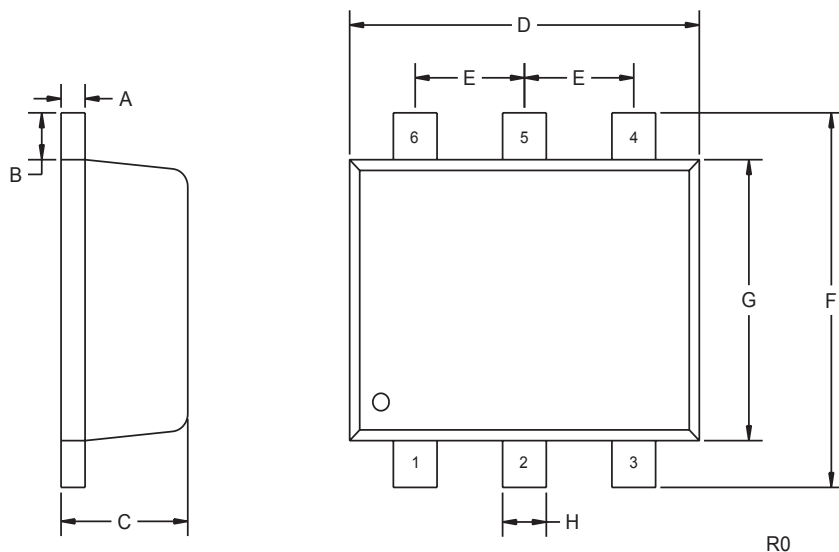
SYMBOL		UNITS
V_{CBO}	80	V
V_{CEO}	60	V
V_{EBO}	5.0	V
I_C	1.0	A
I_B	200	mA
I_{CM}	2.0	A
P_D	250	mW
T_J, T_{stg}	-65 to +150	$^\circ\text{C}$
θ_{JA}	500	$^\circ\text{C/W}$

ELECTRICAL CHARACTERISTICS: ($T_A=25^\circ\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	$V_{CB}=60\text{V}$		100	nA
I_{EBO}	$V_{EB}=4.0\text{V}$		100	nA
BV_{CBO}	$I_C=100\mu\text{A}$	80		V
BV_{CEO}	$I_C=10\text{mA}$	60		V
BV_{EBO}	$I_E=100\mu\text{A}$	5.0		V
$V_{CE(SAT)}$	$I_C=500\text{mA}, I_B=50\text{mA}$		0.20	V
$V_{CE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		0.40	V
$V_{BE(SAT)}$	$I_C=1.0\text{A}, I_B=100\text{mA}$		1.1	V
$V_{BE(ON)}$	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$		1.0	V
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{mA}$	200		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=500\text{mA}$	200	600	
h_{FE}	$V_{CE}=5.0\text{V}, I_C=1.0\text{A}$	50		
h_{FE}	$V_{CE}=5.0\text{V}, I_C=2.0\text{A}$	15		
f_T	$V_{CE}=10\text{V}, I_C=50\text{mA}, f=100\text{MHz}$	150		MHz
C_{ob}	$V_{CB}=10\text{V}, I_E=0, f=1.0\text{MHz}$		10	pF

R2 (7-August 2003)

SOT-563 CASE - MECHANICAL OUTLINE



SYMBOL	DIMENSIONS			
	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.10	0.18
B	0.008		0.20	
C	0.022	0.024	0.56	0.60
D	0.059	0.067	1.50	1.70
E	0.020		0.50	
F	0.061	0.067	1.55	1.70
G	0.047		1.20	
H	0.006	0.012	0.15	0.30

SOT-563 (REV: R0)

LEAD CODE:

- 1) COLLECTOR
 - 2) COLLECTOR
 - 3) BASE
 - 4) EMITTER
 - 5) COLLECTOR
 - 6) COLLECTOR
- Pins 1, 2, 5 and 6 are common.

MARKING CODE: L59

R2 (7-August 2003)